
Feedstock preparing for mc-Si growth

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The paper describes one of the variants of the purification process for silicon feedstock, heavily-doped with arsenic silicon. It presents theoretical calculation results of the method's effectivity. The suggested method includes high-temperature vacuum annealing of melted silicon and subsequent crystal growth by CZ method. We also describe the technique of using this method for the feedstock preparation for multicrystalline silicon ingot growth.

Keywords: *feedstock heavily-doped with arsenic silicon, evaporation, purification by crystallization, vacuum annealing, multicrystalline silicon.*

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